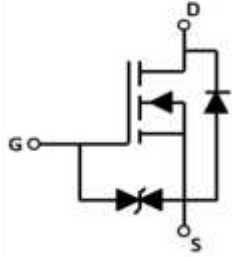
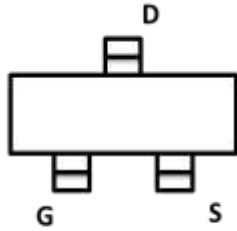


## N-Channel Enhancement Mode Field Effect Transistor



Top View

**SOT-23**



### Product Summary

- $V_{DS}$  20V
- $I_D$  0.9A
- $R_{DS(ON)}$  ( at  $V_{GS}=4.5V$  ) < 250 mohm
- $R_{DS(ON)}$  ( at  $V_{GS}=2.5V$  ) < 350 mohm
- ESD Protected Up to 4.0KV (HBM)

### General Description

- Trench Power LV MOSFET technology
- High Power and current handling capability

### Applications

- Interfacing switching
- Load/Power switching
- Logic Level shift

### ■ Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	$V_{DS}$	20	V
Gate-source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current	$I_D$	$T_A=25^\circ C$ @ Steady State	0.9
		$T_A=70^\circ C$ @ Steady State	0.7
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	3.5	A
Total Power Dissipation @ $T_A=25^\circ C$	$P_D$	0.35	W
Thermal Resistance Junction-to-Ambient @ Steady State	$R_{\theta JA}$	357	$^\circ C/W$
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	$^\circ C$

### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJL3134K	F2	34K.	3000	30000	120000	7" reel



# YJL3134K

## ■ Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±10V, V <sub>DS</sub> =0V		2.5	±10	μA
		V <sub>GS</sub> = ±8V, V <sub>DS</sub> =0V		500	±2000	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.35	0.75	1.1	V
Static Drain-Source On-Resistance	R <sub>D(S)(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =0.5A		120	250	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =0.3A		160	350	
Diode Forward Voltage <sup>C</sup>	V <sub>SD</sub>	I <sub>S</sub> =0.9A, V <sub>GS</sub> =0V			1.2	V
Maximum Body-Diode Continuous Current	I <sub>S</sub>				0.9	A
<b>Dynamic Parameters<sup>B</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHZ		56		pF
Output Capacitance	C <sub>oss</sub>			20		
Reverse Transfer Capacitance	C <sub>rss</sub>			2.5		
<b>Switching Parameters<sup>B</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =10V, I <sub>D</sub> =0.9A		1		nC
Gate Source Charge	Q <sub>gs</sub>			0.28		
Gate Drain Charge	Q <sub>gd</sub>			0.22		
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =0.5A, di/dt=20A/us		0.4		ns
Reverse Recovery Time	t <sub>rr</sub>			14.4		
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =4.5V, V <sub>DD</sub> =10V, R <sub>G</sub> =10Ω, I <sub>D</sub> =500mA		2		ns
Turn-on Rise Time	t <sub>r</sub>			18.8		
Turn-off Delay Time	t <sub>D(off)</sub>			10		
Turn-off Fall Time	t <sub>f</sub>			23		

A. Repetitive Rating: Pulse width limited by maximum junction temperature.

B. These parameters have no way to verify.

C. Pulse Test: Pulse Width ≤ 300us, Duty Cycle ≤ 0.5%.



■ Typical Performance Characteristics

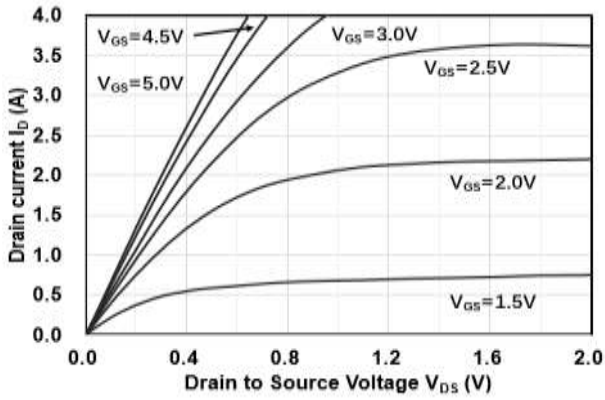


Figure1. Output Characteristics

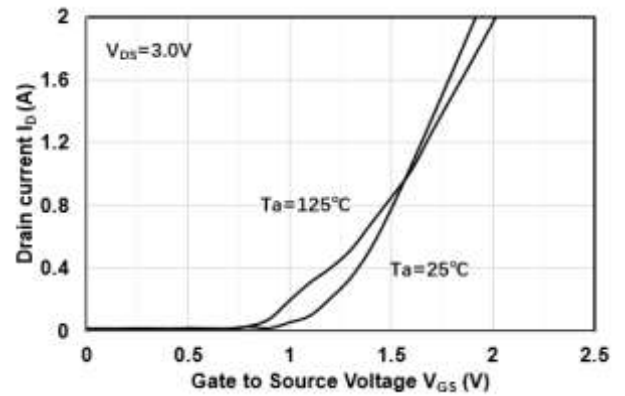


Figure2. Transfer Characteristics

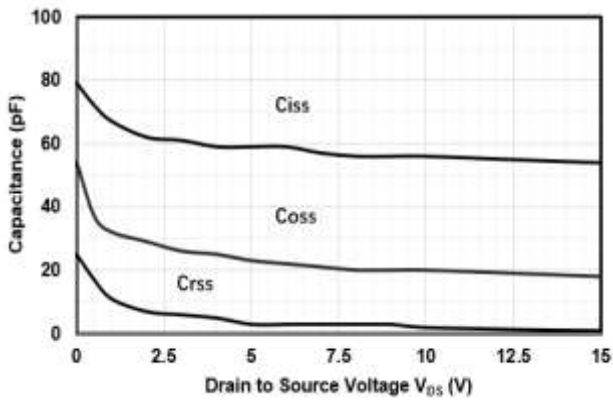


Figure3. Capacitance Characteristics

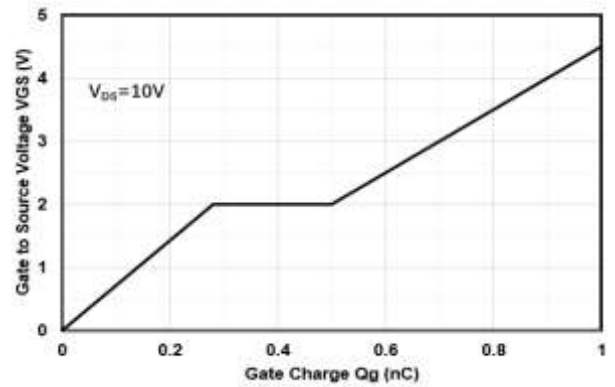


Figure4. Gate Charge

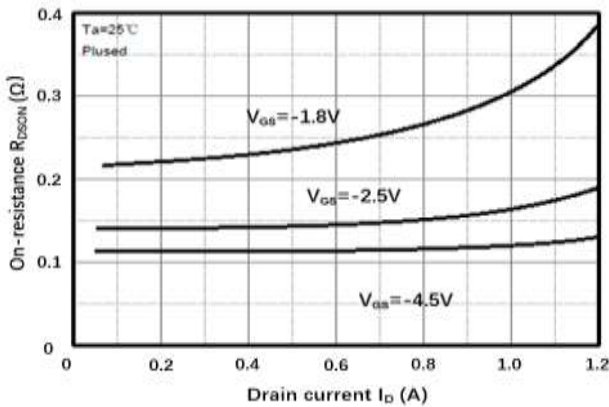


Figure5. Drain-Source on Resistance

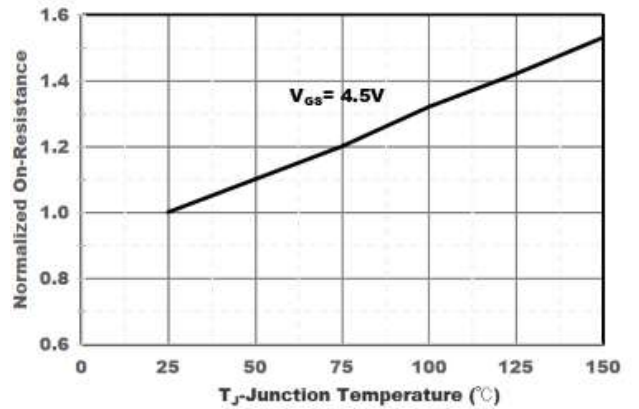


Figure6. Drain-Source on Resistance



# YJL3134K

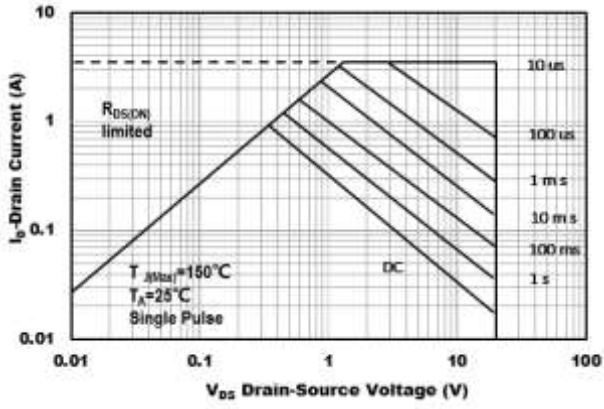


Figure7. Safe Operation Area

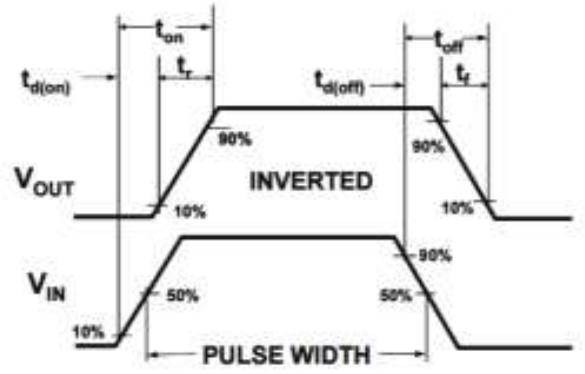
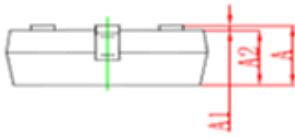
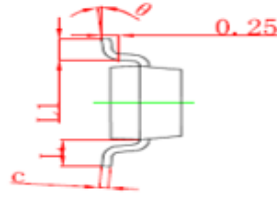
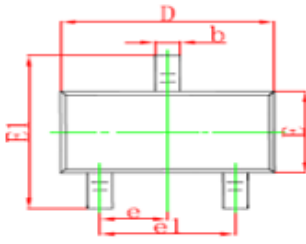


Figure8. Switching wave



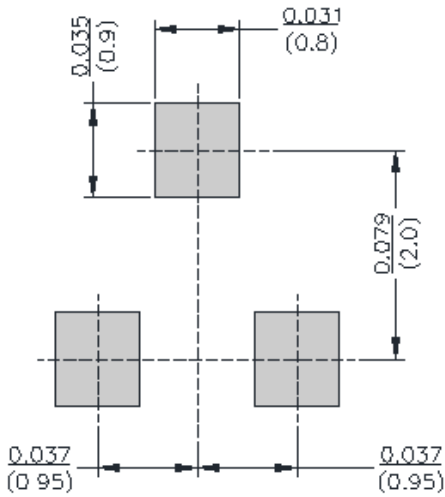
# YJL3134K

## ■SOT-23 Package information



Symbol	Dimensions in Millimeter		Dimensions in Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950Type		0.037Type	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.220REF	
L1	0.300	0.500	0.012	0.020
$\theta$	0°	8°	0°	8°

## ■SOT-23 Suggested Pad Layout





## YJL3134K

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